

2Mb Ultra-Low Power Asynchronous CMOS SRAM

128Kx16 bit

Overview

The N02L1618C1A is an integrated memory device containing a 2 Mbit Static Random Access Memory organized as 131,072 words by 16 bits. The device is designed and fabricated using NanoAmp's advanced CMOS technology to provide both high-speed performance and ultra-low power. The base design is the same as NanoAmp's N02L163WN1A, which is processed to operate at higher voltages. The device operates with a single chip enable (\overline{CE}) control and output enable (\overline{OE}) to allow for easy memory expansion. Byte controls (\overline{UB} and \overline{LB}) allow the upper and lower bytes to be accessed independently. The N02L1618C1A is optimal for various applications where low-power is critical such as battery backup and hand-held devices. The device can operate over a very wide temperature range of -40°C to $+85^{\circ}\text{C}$ and is available in JEDEC standard packages compatible with other standard 128Kb x 16 SRAMs.

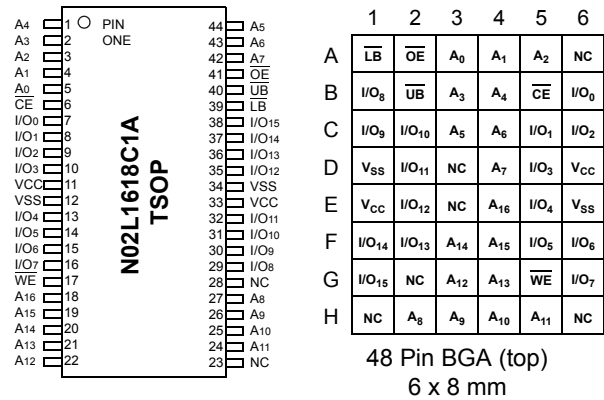
Features

- **Single Wide Power Supply Range**
1.65 to 2.2 Volts
- **Very low standby current**
0.5 μA at 1.8V (Typical)
- **Very low operating current**
1.4mA at 1.8V and 1 μs (Typical)
- **Very low Page Mode operating current**
0.5mA at 1.8V and 1 μs (Typical)
- **Simple memory control**
Single Chip Enable (\overline{CE})
Byte control for independent byte operation
Output Enable (\overline{OE}) for memory expansion
- **Low voltage data retention**
 $V_{cc} = 1.2\text{V}$
- **Very fast output enable access time**
30ns \overline{OE} access time
- **Automatic power down to standby mode**
- **TTL compatible three-state output driver**
- **Compact space saving BGA package available**

Product Family

Part Number	Package Type	Operating Temperature	Power Supply (V_{cc})	Speed	Standby Current (I_{SB}), Max	Operating Current (I_{cc}), Max
N02L1618C1AB	48 - BGA	-40°C to $+85^{\circ}\text{C}$	1.65V - 2.2V	70/85ns @ 1.65V	10 μA	3 mA @ 1MHz
N02L1618C1AB2	Green 48-BGA					
N02L1618C1AT2	Green 44-TSOP2					
N02L1618C1AT	44 - TSOP2					

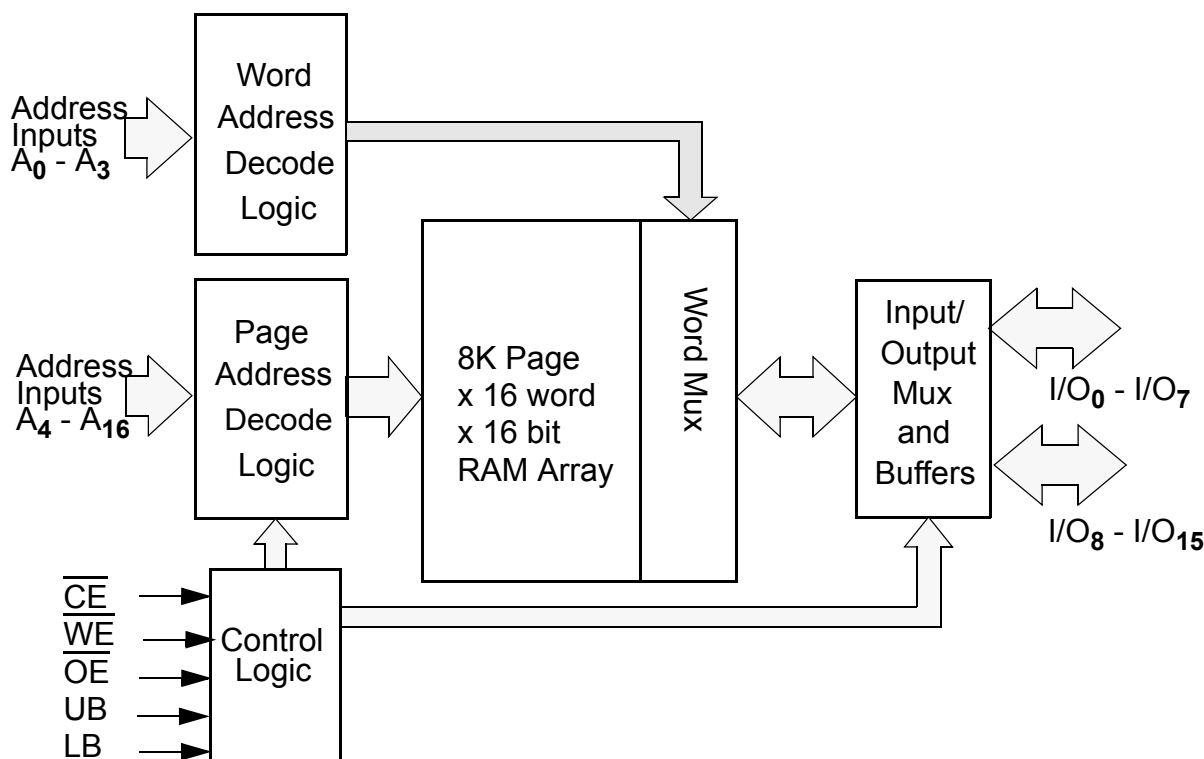
Pin Configurations



Pin Descriptions

Pin Name	Pin Function
A ₀ -A ₁₆	Address Inputs
WE	Write Enable Input
CE	Chip Enable Input
OE	Output Enable Input
LB	Lower Byte Enable Input
UB	Upper Byte Enable Input
I/O ₀ -I/O ₁₅	Data Inputs/Outputs
NC	Not Connected
V _{CC}	Power
V _{SS}	Ground

Functional Block Diagram



Functional Description

\overline{CE}	\overline{WE}	\overline{OE}	\overline{UB}	\overline{LB}	$I/O_0 - I/O_{15}^1$	MODE	POWER
H	X	X	X	X	High Z	Standby ²	Standby
L	X	X	H	H	High Z	Standby ²	Standby
L	L	X ³	L ¹	L ¹	Data In	Write ³	Active
L	H	L	L ¹	L ¹	Data Out	Read	Active
L	H	H	L ¹	L ¹	High Z	Active	Active

- When \overline{UB} and \overline{LB} are in select mode (low), $I/O_0 - I/O_{15}$ are affected as shown. When \overline{LB} only is in the select mode only $I/O_0 - I/O_7$ are affected as shown. When \overline{UB} is in the select mode only $I/O_8 - I/O_{15}$ are affected as shown.
- When the device is in standby mode, control inputs (\overline{WE} , \overline{OE} , \overline{UB} , and \overline{LB}), address inputs and data input/outputs are internally isolated from any external influence and disabled from exerting any influence externally.
- When \overline{WE} is invoked, the \overline{OE} input is internally disabled and has no effect on the circuit.

Capacitance¹

Item	Symbol	Test Condition	Min	Max	Unit
Input Capacitance	C_{IN}	$V_{IN} = 0V$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$		8	pF
I/O Capacitance	$C_{I/O}$	$V_{IN} = 0V$, $f = 1 \text{ MHz}$, $T_A = 25^\circ\text{C}$		8	pF

- These parameters are verified in device characterization and are not 100% tested

Absolute Maximum Ratings¹

Item	Symbol	Rating	Unit
Voltage on any pin relative to V _{SS}	V _{IN,OUT}	-0.3 to V _{CC} +0.3	V
Voltage on V _{CC} Supply Relative to V _{SS}	V _{CC}	-0.3 to 3.0	V
Power Dissipation	P _D	500	mW
Storage Temperature	T _{STG}	-40 to 125	°C
Operating Temperature	T _A	-40 to +85	°C
Soldering Temperature and Time	T _{SOLDER}	240°C, 10sec(Lead only)	°C

1. Stresses greater than those listed above may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

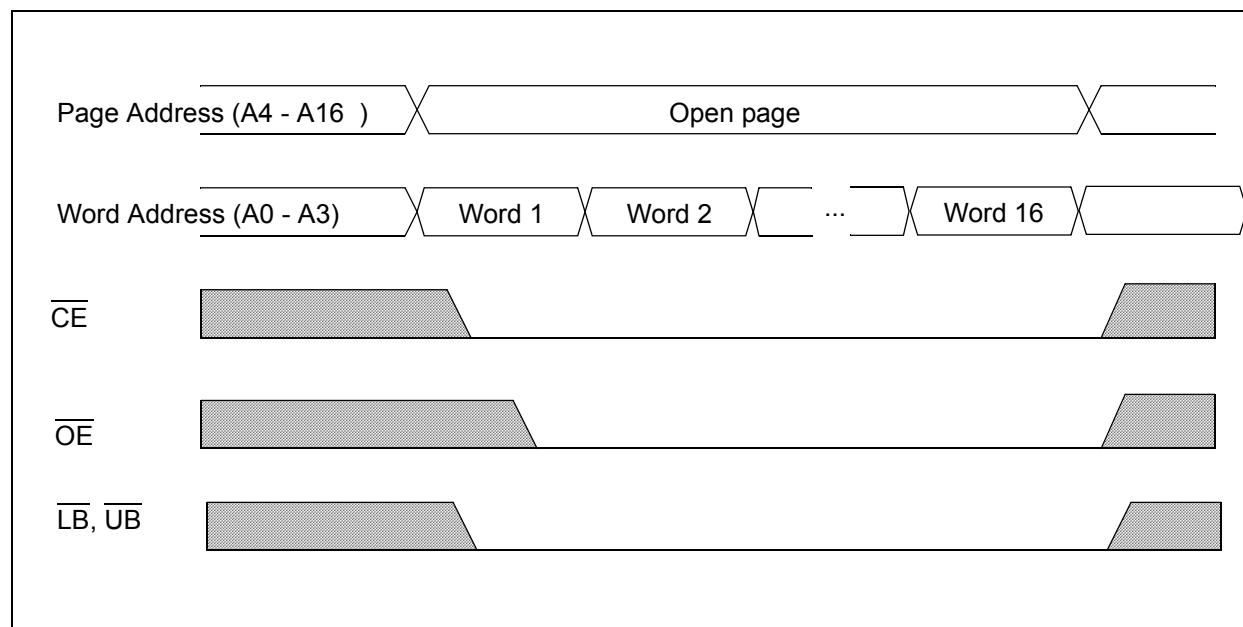
Operating Characteristics (Over Specified Temperature Range)

Item	Symbol	Test Conditions	Min.	Typ ¹	Max	Unit
Supply Voltage	V _{CC}		1.65	1.8	2.2	V
Data Retention Voltage	V _{DR}	Chip Disabled ²	1.2		2.2	V
Input High Voltage	V _{IH}		0.7V _{CC}		V _{CC} +0.3	V
Input Low Voltage	V _{IL}		-0.3		0.3V _{CC}	V
Output High Voltage	V _{OH}	I _{OH} = 0.2mA	V _{CC} -0.2			V
Output Low Voltage	V _{OL}	I _{OL} = -0.2mA			0.3	V
Input Leakage Current	I _{LI}	V _{IN} = 0 to V _{CC}			0.5	μA
Output Leakage Current	I _{LO}	\overline{OE} = V _{IH} or Chip Disabled			0.5	μA
Read/Write Operating Supply Current @ 1 μs Cycle Time ²	I _{CC1}	V _{CC} =2.2 V, V _{IN} =V _{IH} or V _{IL} Chip Enabled, I _{OUT} = 0		1.4	3.0	mA
Read/Write Operating Supply Current @ 70 ns Cycle Time ²	I _{CC2}	V _{CC} =2.2 V, V _{IN} =V _{IH} or V _{IL} Chip Enabled, I _{OUT} = 0		8.0	17.0	mA
Page Mode Operating Supply Current @ 70ns Cycle Time ² (Refer to Power Savings with Page Mode Operation diagram)	I _{CC3}	V _{CC} =2.2V, V _{IN} =V _{IH} or V _{IL} Chip Enabled, I _{OUT} = 0		2.0	4.0	mA
Read/Write Quiescent Operating Supply Current ³	I _{CC4}	V _{CC} =2.2V, V _{IN} =V _{IH} or V _{IL} Chip Enabled, I _{OUT} = 0, f = 0			0.1	mA
Maximum Standby Current ³	I _{SB1}	V _{IN} = V _{CC} or 0V Chip Disabled t _A = 85°C, V _{CC} = 2.2 V		0.5	10.0	μA
Maximum Data Retention Current ³	I _{DR}	V _{CC} = 1.2V, V _{IN} = V _{CC} or 0 Chip Disabled, t _A = 85°C			5.0	μA

1. Typical values are measured at V_{CC}=V_{CC} Typ., T_A=25°C and are not 100% tested.

2. This parameter is specified with the outputs disabled to avoid external loading effects. The user must add current required to drive output capacitance expected in the actual system.

3. This device assumes a standby mode if the chip is disabled (\overline{OE} high). In order to achieve low standby current all inputs must be within 0.2 volts of either V_{CC} or V_{SS}

Power Savings with Page Mode Operation ($\overline{WE} = V_{IH}$)

Note: Page mode operation is a method of addressing the SRAM to save operating current. The internal organization of the SRAM is optimized to allow this unique operating mode to be used as a valuable power saving feature.

The only thing that needs to be done is to address the SRAM in a manner that the internal page is left open and 16-bit words of data are read from the open page. By treating addresses A0-A3 as the least significant bits and addressing the 16 words within the open page, power is reduced to the page mode value which is considerably lower than standard operating currents for low power SRAMs.

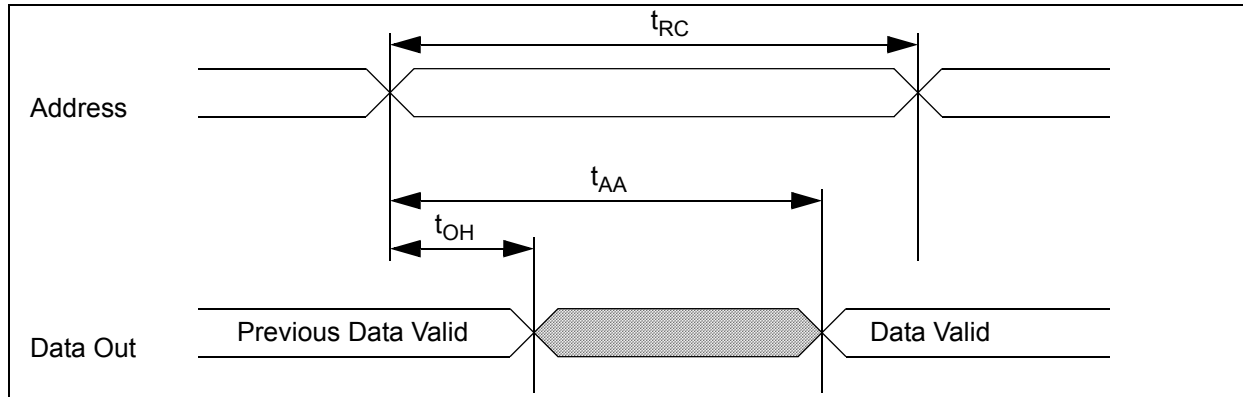
Timing Test Conditions

Item	
Input Pulse Level	$0.1V_{CC}$ to $0.9V_{CC}$
Input Rise and Fall Time	5ns
Input and Output Timing Reference Levels	$0.5V_{CC}$
Output Load	CL = 30pF
Power Supply Voltage	1.65 - 2.2V
Operating Temperature	-40 to +85 °C

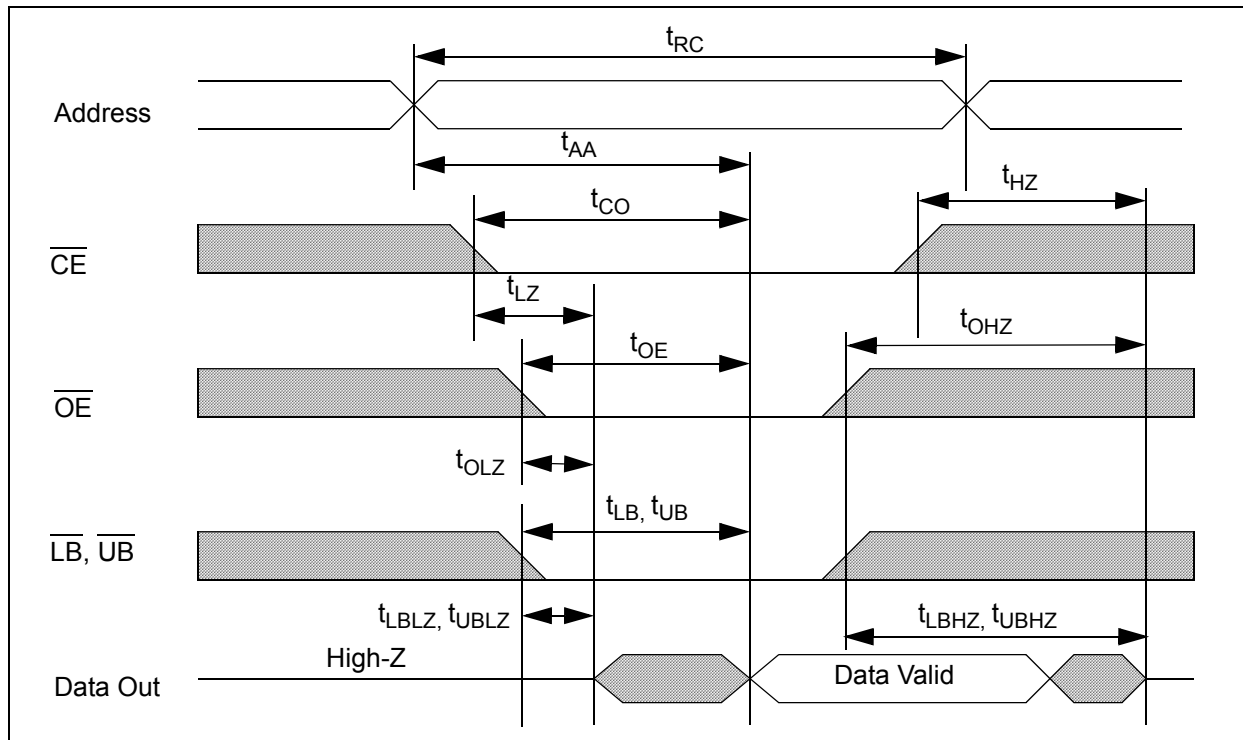
Timing

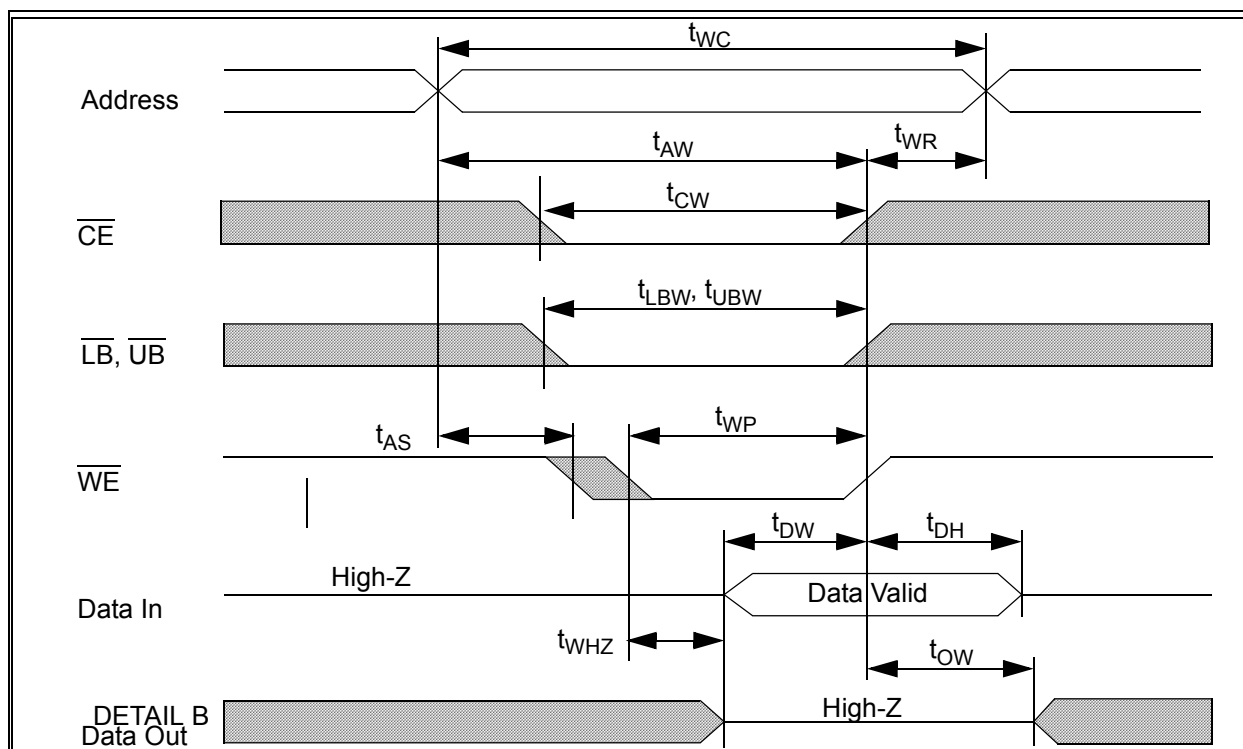
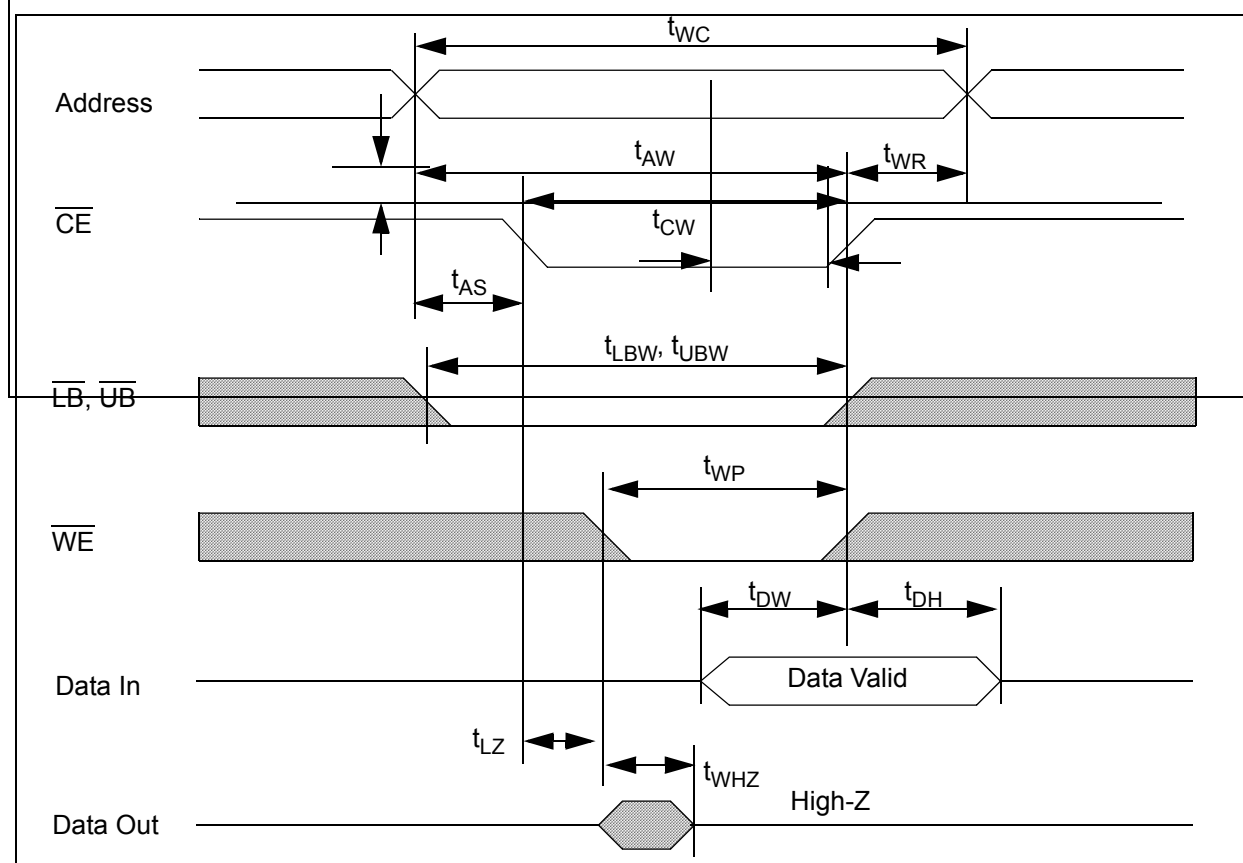
Item	Symbol	85ns		70ns		Units
		Min.	Max.	Min.	Max.	
Read Cycle Time	t_{RC}	85		70		ns
Address Access Time	t_{AA}		85		70	ns
Chip Enable to Valid Output	t_{CO}		85		70	ns
Output Enable to Valid Output	t_{OE}		30		25	ns
Byte Select to Valid Output	t_{LB}, t_{UB}		85		70	ns
Chip Enable to Low-Z output	t_{LZ}	10		10		ns
Output Enable to Low-Z Output	t_{OLZ}	5		5		ns
Byte Select to Low-Z Output	t_{LBZ}, t_{UBZ}	10		10		ns
Chip Disable to High-Z Output	t_{HZ}		30		25	ns
Output Disable to High-Z Output	t_{OHZ}		30		25	ns
Byte Select Disable to High-Z Output	t_{LBHZ}, t_{UBHZ}		30		25	ns
Output Hold from Address Change	t_{OH}	5		5		ns
Write Cycle Time	t_{WC}	85		70		ns
Chip Enable to End of Write	t_{CW}	50		40		ns
Address Valid to End of Write	t_{AW}	50		40		ns
Byte Select to End of Write	t_{LBW}, t_{UBW}	50		40		ns
Write Pulse Width	t_{WP}	50		40		ns
Address Setup Time	t_{AS}	0		0		ns
Write Recovery Time	t_{WR}	0		0		ns
Write to High-Z Output	t_{WHZ}		25		20	ns
Data to Write Time Overlap	t_{DW}	40		40		ns
Data Hold from Write Time	t_{DH}	0		0		ns
End Write to Low-Z Output	t_{OW}	10		10		ns

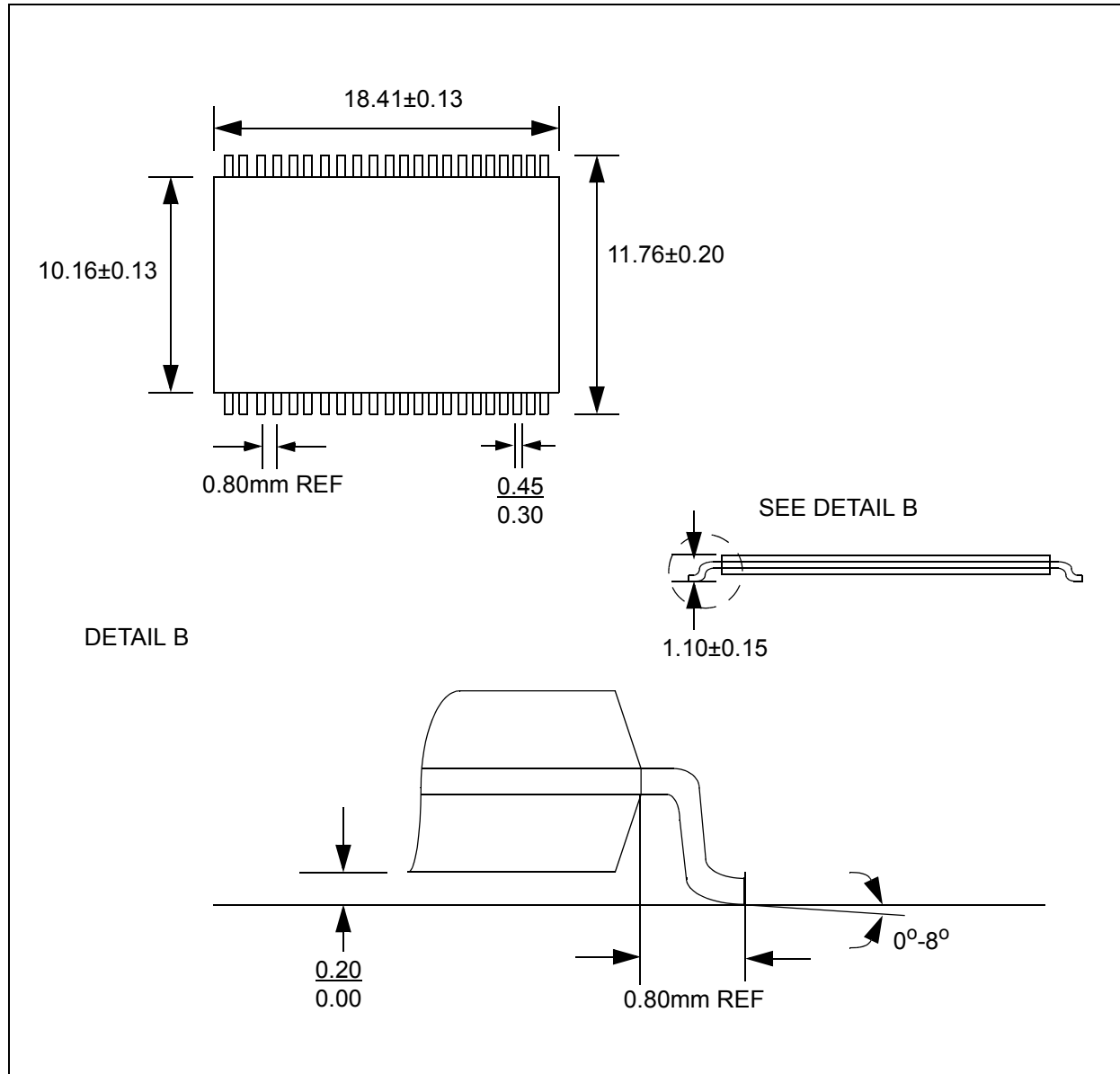
Timing of Read Cycle ($\overline{CE} = \overline{OE} = V_{IL}, \overline{WE} = V_{IH}$)



Timing Waveform of Read Cycle ($\overline{WE} = V_{IH}$)

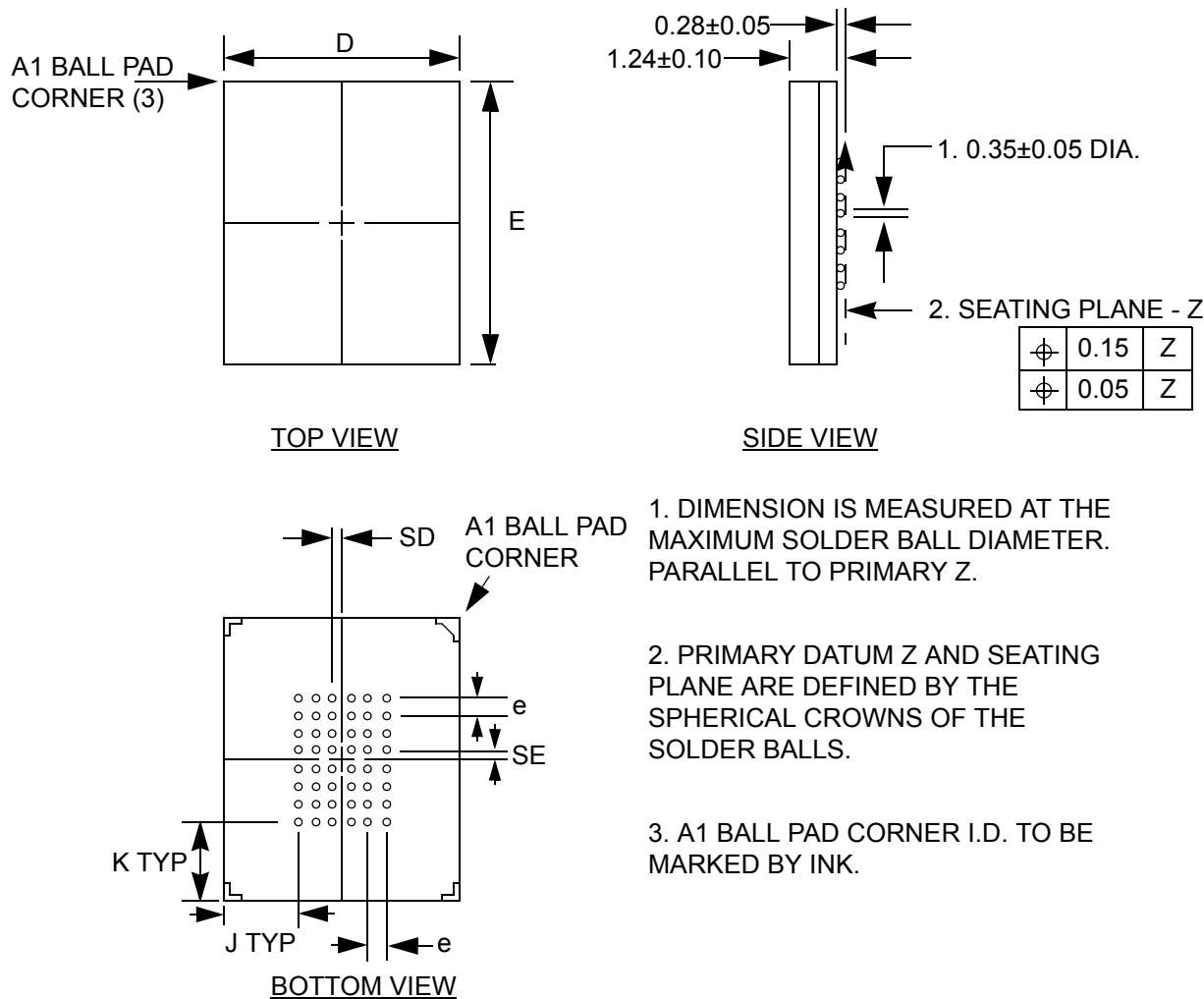


Timing Waveform of Write Cycle ($\overline{\text{WE}}$ control)Timing Waveform of Write Cycle ($\overline{\text{CE}}$ Control)

44-Lead TSOP II Package (T44)**Note:**

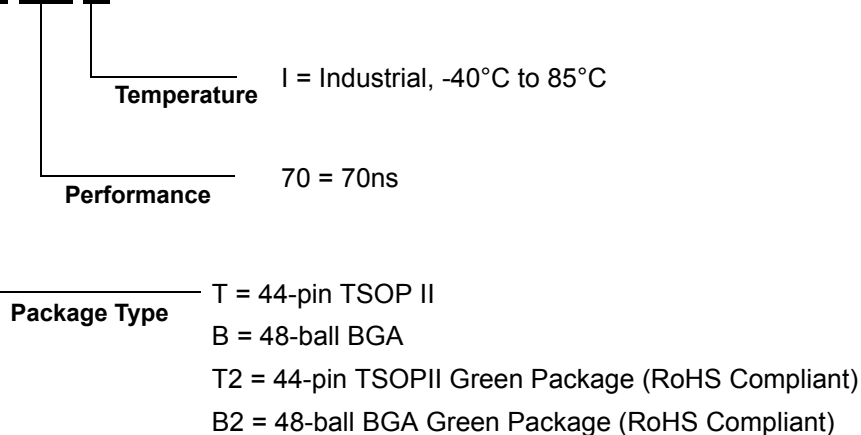
1. All dimensions in inches (Millimeters)
2. Package dimensions exclude molding flash

Ball Grid Array Package



Dimensions (mm)

D	E	e = 0.75				BALL MATRIX TYPE
		SD	SE	J	K	
6±0.10	8±0.10	0.375	0.375	1.125	1.375	FULL

Ordering Information**N02L1618C1AX-XX X****Revision History**

Revision #	Date	Change Description
A	Apr. 2003	Initial Release
B	Nov. 2005	Added TSOP II Green Pkg. , Green Pkg. Part # and RoHS Compliant

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